IN THE SPECIFICATION:

Please replace the paragraph at page 7, line 22 – page 8, line 8 with the following amended paragraph:

The chamber bottom 206 is shaped to accommodate the substantially circular base of the substrate support 216 and the substantially circular chamber outlet 208. As shown in Figure 3, the chamber wall 204 is shaped to provide an internal volume defined by first and second substantially semi-cylindrical regions 204A ~~204a~~, 204B ~~204b~~ and by side wall portions 204C ~~204c~~ extending between the first and second semi-cylindrical regions. The first semi-cylindrical region 204A ~~204a~~ has sufficient space for mounting the substrate support 216 and the second semi-cylindrical region 204B ~~204b~~ encloses the chamber outlet 208. The first semi-cylindrical region 204A ~~204a~~ is spaced from an outer surface of the substrate support 216 to provide a gas passageway around the body of the substrate support 216. The second semi-cylindrical region 204B ~~204b~~ surrounds a portion of the exhaust region above the chamber outlet 208. The side wall portions 204C ~~204c~~ defines an exhaust passageway connecting the gas passageway around the body of the substrate support 216 to the exhaust region above the chamber outlet 208. The internal volume includes sufficient space for one or more liners defining a cylindrical processing region and cylindrical exhaust region as described in more detail below. In one embodiment as shown in Figure [[2]] 3, the side wall portions 204C ~~204c~~ substantially eliminates any restriction of the conductance (i.e., effectively maximizes conductance) between the gas passageway around the body of the substrate support 216 and the exhaust region above the chamber outlet 208.

Please replace the paragraph at page 8, lines 9-12 with the following amended paragraph:

Generally, the diameter of the semi-cylindrical section 204A is larger than the diameter of the semi-cylindrical section 204B. However, if a substantially larger vacuum

pump needs to be accommodated, the diameter of section 204B may need to be ~~enlarge~~ enlarged, perhaps even beyond that of section 204A.

Please replace the paragraph at page 8, lines 13-22 with the following amended paragraph:

A slit 230 for facilitating substrate transfers into and out of the chamber is disposed on the chamber wall 204 at a position proximate the substrate support 216 and above the substrate supporting surface 218. A slit valve 232 is disposed adjacent to the slit 230 and the chamber wall 204 to facilitate substrate transfers into and out of the chamber (*i.e.*, when slit valve is open) and to maintain desired chamber vacuum levels during processing (*i.e.*, when slit valve is closed). As shown in Figure 2, the slit valve 232 comprises a plasma isolation slit valve which is moveably disposed against an interior surface of the chamber wall 204. The plasma isolation slit valve is attached to a slit valve actuator 233, such as a pneumatic actuator or other motors, disposed through the chamber bottom 206. The slit valve actuator 233 moves the slit valve 232 between an open position and a closed position.

Please replace the paragraph at page 9, line 29 – page 10, line 2 with the following amended paragraph:

The lower liner 254 includes a wall portion 256 that lines a lower interior portion of the chamber wall 204. The lower liner 254 may also include a bottom portion 258 that covers substantially the chamber bottom 206 that may be exposed to processing gases. The bottom portion 258 has holes or openings 260 and 262 to accommodate the substrate support 216 and the outlet 208, respectively.

Please replace the paragraph at page 12, lines 10-23 with the following amended paragraph:

Figures ~~6a-c~~ 6A-C are top views of embodiments of the chamber of the invention. Figure ~~6a~~ 6A shows one embodiment of the chamber where the side wall portions ~~204c~~ 204C are substantially tangent to the first and second cylindrical regions. In this embodiment, the side wall portions ~~204c~~ 204C effectively maximizes the conductance between the gas passageway around the body of the substrate support 216 and the exhaust region above the chamber outlet 208. In one embodiment for a chamber configured to process a 300 mm substrate, a diameter d3 (e.g., about 560 mm) of the first cylindrical region is at least about 180 mm (about 47%) wider than a diameter d1 (e.g., about 380 mm) of the body of the substrate support 216 to provide sufficient spacing between the chamber wall and the substrate support to enhance uniform flow of process gases to the chamber outlet, and the second cylindrical region surrounding the chamber outlet has a diameter d4 of about 340 mm to accommodate attachment of a 320 mm outlet valve. In this embodiment, the diameter d3 (about 560 mm) of the first cylindrical region is at least about 65% wider than a diameter d4 (about 340 mm) of the second cylindrical region.

Please replace the paragraph at page 13, lines 3-7 with the following amended paragraph:

Figure ~~6b~~ 6B shows one embodiment of the chamber where the side wall portions ~~204c~~ 204C are substantially tangent to the second cylindrical region and abut the first cylindrical region. The side wall portions ~~204c~~ 204C may be substantially parallel. In one embodiment, the width ~~w1~~ W1 between the inner surfaces of the side wall portions ~~204c~~ 204C adjacent the first cylindrical region is at least as wide as a diameter d1 of the body of the substrate support 216.

Please replace the paragraph at page 13, lines 8-16 with the following amended paragraph:

Figure ~~6c~~ 6C shows one embodiment of the chamber where the side wall portions ~~204c~~ 204C abut the two cylindrical regions. In the embodiment shown in Figure ~~6c~~ 6C, the inner surfaces of the side wall portions ~~204c~~ 204C are disposed along lines that are tangent to a circumference of the body of the substrate support 216 and an inner circumference of the chamber outlet 208. In one embodiment, the width ~~w1~~ W1 between the inner surfaces of the side wall portions ~~204c~~ 204C adjacent the first cylindrical region is at least as wide as a diameter d1 of the body of the substrate support 216. Also, the width ~~w2~~ W2 between the inner surfaces of the side wall portions ~~204c~~ 204C adjacent the second cylindrical region is at least as much as the internal diameter d1 of the chamber outlet 208.

Please replace the paragraph at page 13, line 29 – page 14, line 12 with the following amended paragraph:

The multi-purpose chamber 500 includes a liner removably disposed in the chamber which configures the chamber for particular processing, for example, an etch process. The liner is made of nickel, aluminum, or other metals or metal alloys appropriate for plasma processing, and may also include an anodized aluminum surface. The liner may be a single piece construction or a multi-piece construction. As shown in Figure 8, the liner is a one-piece liner 652. The liner 652 includes a wall portion 672 that lines the chamber wall 204. The liner 652 may also include a bottom portion 658 that covers substantially the chamber bottom 206 that may be exposed to processing gases. The bottom portion ~~668~~ 658 has holes or openings 660 and 662 to accommodate the substrate support 216 and the outlet 208, respectively. The liner 652 includes a plasma confinement portion 664 that surrounds a processing region above the substrate support 216. The plasma confinement portion 664 has a substantially cylindrical shape to match a round substrate support 216 and is disposed substantially concentrically with the substrate support 216 to form a substantially uniform passage

way between the inner surface of the plasma confinement portion 664 and the outer surface of the substrate support 216.